

T10A series Sibod™

FEATURES

- Glass passivated junction
- High current diverting capability (150A, 8x20μs)
- Low capacitance, less than 100pF
- UL recognized
- Automatic reset
- Does not degrade

APPLICATION

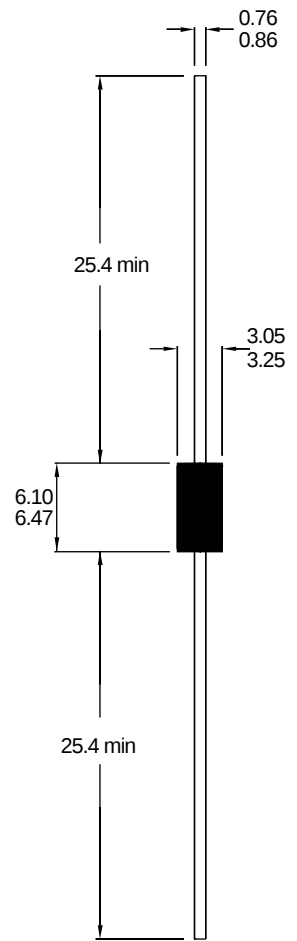
- Bi-directional device for telephone and line card protection

ELECTRICAL CHARACTERISTICS (Tamb = +25°C)

SYMBOL	PARAMETER
V _{RM}	Stand-off Voltage
V _{BR}	Breakdown Voltage
I _H	Holding Current
V _R	Continuous Reverse Voltage.

ABSOLUTE RATINGS (limiting values) (T_j = + 25°C)L = 10mm

SYMBOL	PARAMETER	VALUE	UNIT
	Power Dissipation on Infinite Heatsink T _{amb} = 50°C	1.7	W
I _{pp}	Peak Pulse Current 10x1000μsec 10/700 1.5KV 8-20 us expo	50 37.5 100	A
I _{TSM}	Non Repetitive Surge Peak on-state Current tp = 20 ms	30	A
di/dt	Critical Rate of Rise of on-state Current Non repetitive	100	A/μS
T _{stg} T _j	Storage and Operating Junction Temperature Range	-40 to 150 150	°C °C
T _L	Maximum Lead Temperature for soldering during 10s at 4mm from Case	230	°C



All dimensions in mm.

THERMAL RESISTANCES

SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-i)} R _{th(j-a)}	Junction-leads on Infinite Heatsink L = 10mm Junction-ambient on Printed Circuit	60 100	°C/W °C/W

All parameters are tested using Fet Test™ Model 3600

DEVICE TYPE	I _{RM} @ V _{RM} max		I _r @ V _R max		V _{BO} @ I _{BO} max		I _H min
	μA	V	μA	V	V	mA	
T10A62	2	56	50	62	82	800	150
T10A68	2	61	50	68	90	800	150
T10A100	2	90	50	100	133	800	150
T10A120	2	108	50	120	160	800	150
T10A130	2	117	50	130	173	800	150
T10A180	2	162	50	180	240	800	150
T10A200	2	180	50	200	267	800	150
T10A220	2	198	50	220	293	800	150
T10A240	2	216	50	240	320	800	150
T10A270	2	243	50	270	360	800	150

ORDERING INFORMATION

T10A

Voltage

Packaging Option

B = Bulk (1000 pcs)

T = Tape and reeled (5000 pcs)

All products are sold to the commercial specifications shown, for any additional reliability testing or extended parameters, please consult the factory.

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